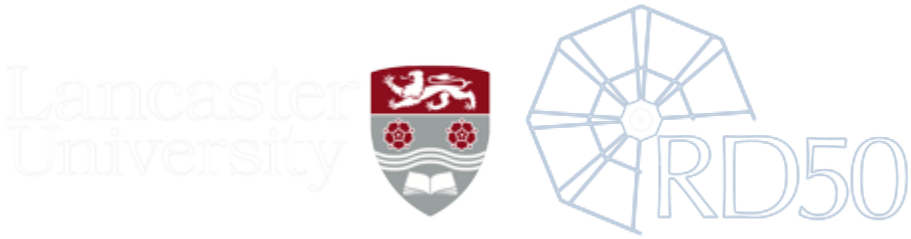

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DLTS studies of point and cluster defects in □- and neutron-irradiated p-type Si pad diodes

Thursday, 13 June 2019 10:20 (20 minutes)

P-type silicon pad diodes with variation of material type - EPI, FZ and CZ - and resistivity (boron concentration) have been irradiated with reactor neutrons with different fluences in JSI, Ljubljana, Slovenia and with gamma rays (Co-60) in BGS, Wiehl, Germany. Comparative investigation of the radiation induced defects by Thermally Stimulated Current (TSC) and Deep Level Transient Spectroscopy (DLTS) techniques have been performed. The obtained results will be presented and discussed.

Primary authors: GURIMSKAYA, Yana (CERN); MATEU, Isidre (CERN); UDESEN, Soren (Aarhus University (DK)); DIAS DE ALMEIDA, Pedro (Universidad de Cantabria and CSIC (ES)); FERNANDEZ GARCIA, Marcos (Universidad de Cantabria and CSIC (ES)); MOLL, Michael (CERN)

Presenter: GURIMSKAYA, Yana (CERN)

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